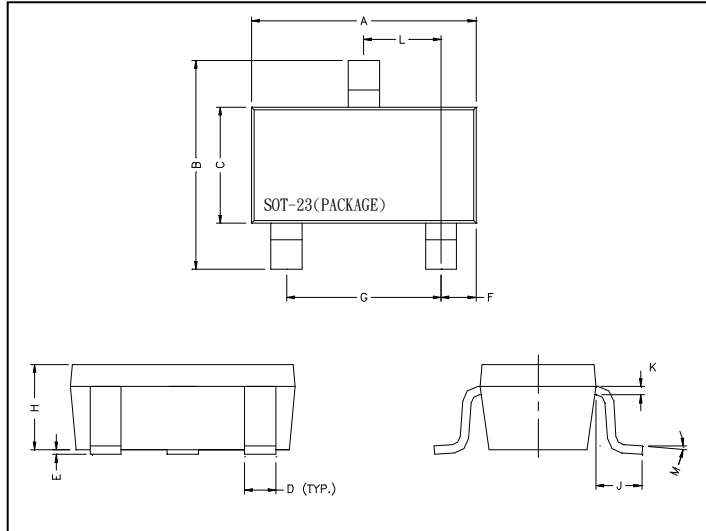


GBAS40 thru GBAS40-06

Description

Silicon Schottky Barrier Double Diodes.

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Marking :

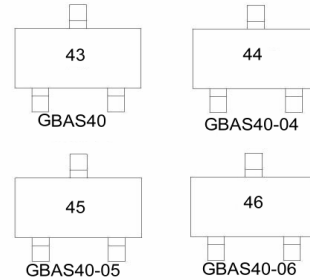
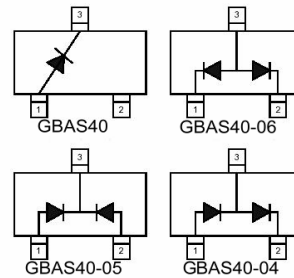


Diagram:



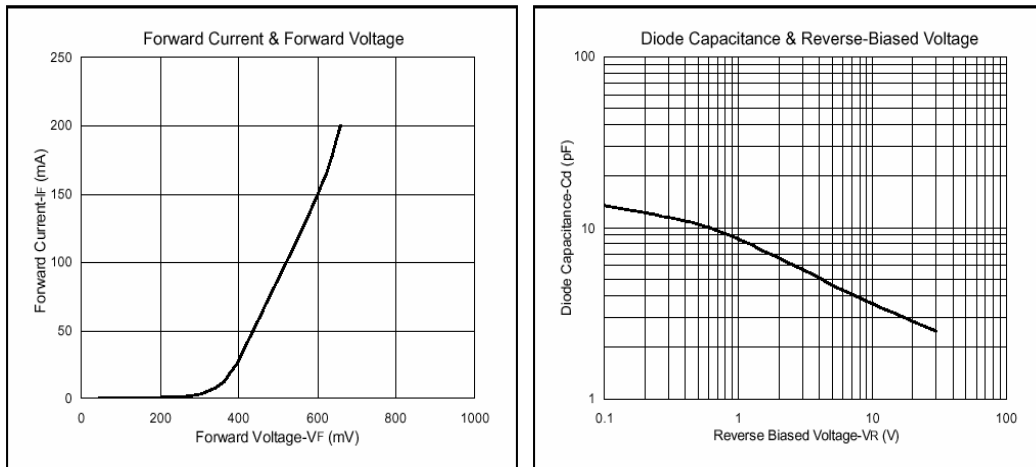
Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	40	V
Forward Continuous Current at Tamb=25°C	I _F	200	mA
Surge Forward Current at tp < 1s, Tamb=25°C	I _{FSM}	600	mA
Thermal Resistance Junction to Ambient Air	R _{thJA}	430	°C/W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Power Dissipation at Ta = 25°C	PD	200	mW

Characteristics at Ta = 25°C

characteristics	Symbol	Min	Max.	Unit	Test Conditions
Reverse breakdown voltage	V(BR)R	40	-	V	IR=10uA
Forward Voltage	VF	Pulse Test tp <300us			
		-	380	mV	IF=1mA
		-	1000	mV	IF=40mA
Leakage Current	IR	Pulse Test tp <300us			
		-	200	nA	VR=30V
Total Capacitance	CT	-	5	pF	VR=0V, f=1MHz
Reverse Recover Time	Trr	-	5	ns	IF=IR=10mA, RL=100Ω measured at Irr =1mA

Characteristics Curve

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